

ON Semiconductor DATA SHEET

N-Channel Silicon MOSFET

3LN03M—General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · High-speed switching.
- 2.5V drive.
- High ESD Voltage (TYP 300V)
 [Built-in one side diode for protection between Gate-to-Source].

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage (*1)	VGSS		10	V
Drain Current (DC)	ID		0.35	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	1.4	Α
Allowable Power Dissipation	PD		0.15	Α
Channel Temperature	Tch		150	Α
Storage Temperature	Tstg		-55 to +150	W

^{(*1):} Note, when designing a circuit using this product, that it has a gate (oxide film) protection diode connected only between its gate and source.

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	IDSS	VDS=30V, VGS=0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =8V, V _{DS} =0			1	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =100μA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=180mA	0.36	0.6		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =180mA, V _{GS} =4V		0.7	0.9	Ω
	RDS(on)2	I _D =90mA, V _G S=2.5V		0.8	1.15	Ω
	RDS(on)3	ID=10mA, VGS=1.5V		1.6	2.4	Ω
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		30		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		7		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		3.5		pF

Marking: YG Continued on next page.

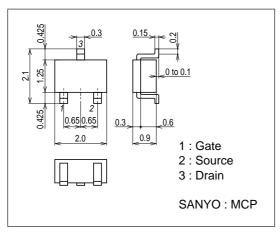
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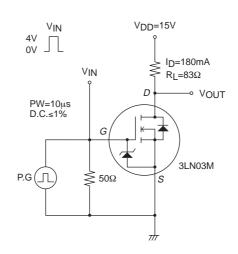
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		8		ns
Rise Time	t _r	See specified Test Circuit.		4.5		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		11		ns
Fall Time	tf	See specified Test Circuit.		6		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =350mA		1		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =350mA		0.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =350mA		0.2		nC
Diode Forward Voltage	V _{SD}	I _S =350mA, V _{GS} =0		0.88	1.2	V

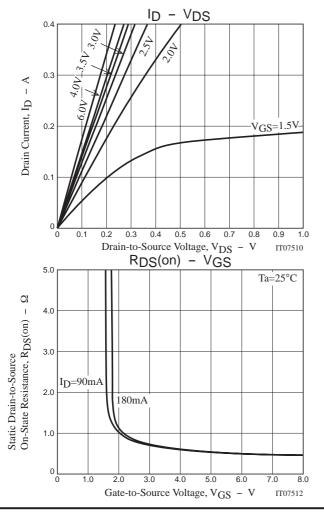
Package Dimensions

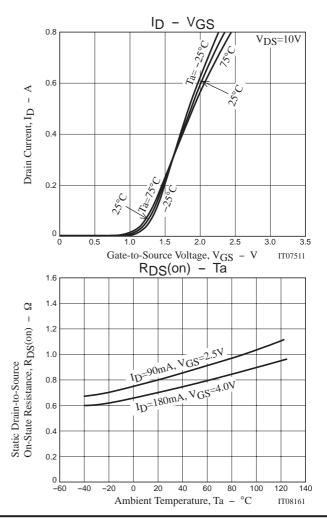
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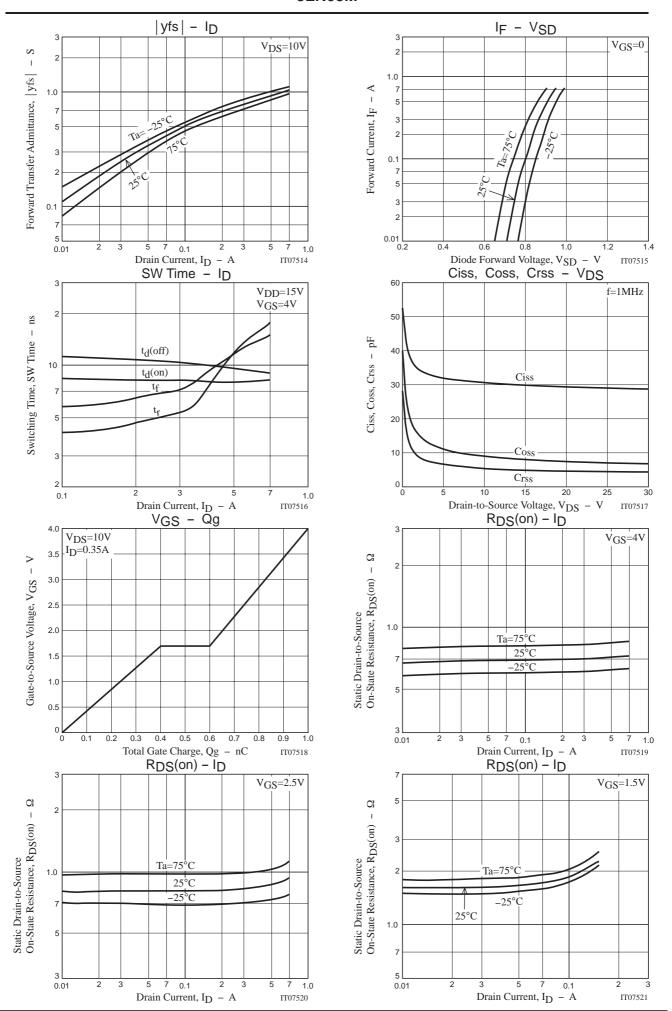


Switching Time Test Circuit

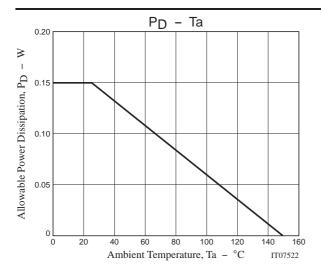








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